

APPLICANT(S): WILK Brian, et al.
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ASSIGNEE: Intel Corporation
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Amendments to the Claims

The following listing of claims replaces all prior versions and listings of claims in the application:

Listing of Claims

- 1 (Currently Amended) A method comprising:
attaching securing a supported surface of a semiconductor wafer to a perforated surface of a wafer support system; and
trapping inside one or more cavities of said wafer support system by causing a supported surface of said semiconductor wafer to be at a lower gas pressure than a gas pressure at an exposed surface of said semiconductor wafer.
- 2 (Currently Amended) The method of claim 1, wherein ~~causing said supported surface to be at~~ trapping said lower gas pressure includes at least:
placing ~~said supported surface of~~ said semiconductor wafer with in contact with a ~~perforated surface of~~ said wafer support system inside a vacuum chamber;
reducing a gas pressure inside said vacuum chamber to substantially said lower gas pressure;
sealing an opposite surface of said wafer support system; and
removing said wafer support system and said secured semiconductor wafer from said vacuum chamber
3. (Currently Amended) The method of claim 1, wherein ~~causing said supported surface to be at~~ trapping said lower gas pressure includes at least:
placing ~~said supported surface of~~ said semiconductor wafer with in contact with a ~~perforated surface of~~ said wafer support system in a first environment at a first temperature;
sealing an opposite surface of said wafer support system; and
removing said wafer support system and said secured semiconductor wafer from said first environment to a second environment at a second temperature that is lower than said first temperature.

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4. **(Currently Amended)** The method of claim 1, wherein ~~causing said supported surface to be at~~ trapping said lower gas pressure includes at least:
 - pushing a flexible surface of said wafer support system inwards towards a perforated surface of said wafer support system;
 - placing said supported surface of said semiconductor wafer in contact with said perforated surface of said wafer support system; and
 - releasing said flexible surface.
5. **(Currently Amended)** The method of claim 1, wherein ~~causing said supported surface to be at~~ trapping said lower gas pressure includes at least:
 - placing said supported surface of said semiconductor wafer in contact with a perforated surface of said wafer support system; and
 - pulling an opposite surface of said support system outwards away from said perforated surface.
6. **(Previously Presented)** The method of claim 1, further comprising:
 - releasing said semiconductor wafer from said wafer support system by increasing said lower gas pressure.
7. **(Previously Presented)** The method of claim 6, wherein increasing said lower gas pressure includes at least:
 - removing an opposite surface of said wafer support system.
8. **(Previously Presented)** The method of claim 6, wherein increasing said lower gas pressure includes at least:
 - pushing a flexible surface of said wafer support system inwards towards said semiconductor wafer.
9. **(Previously Presented)** The method of claim 1, further comprising:
 - releasing said semiconductor wafer from said wafer support system by causing said exposed surface to be at a pressure lower than or substantially equal to said lower gas pressure.

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10. **(Previously Presented)** The method of claim 1, further comprising:
releasing one or more dies of said semiconductor wafer from said wafer support system by increasing said lower gas pressure on the supported surface of said one or more dies while maintaining said lower gas pressure on the supported surface of other portions of said semiconductor wafer.
11. **(Previously Presented)** The method of claim 10, wherein increasing said lower gas pressure on the supported surface of said one or more dies includes at least:
pushing one or more portions of a flexible surface of said wafer support system inwards towards said one or more dies of said semiconductor wafer.
12. **(Previously Presented)** The method of claim 10, wherein increasing said lower gas pressure on the supported surface of said one or more dies includes at least:
piercing one or more portions of a flexible surface of said wafer support system corresponding to said one or more dies of said semiconductor wafer.
13. **(Currently Amended)** The method of claim 10, further comprising:
separating one of said one or more dies from said semiconductor wafer by coupling a die picking tool ~~picker~~ to the exposed surface of said one of said one or more dies.